

## Supplementary Material

### Physics infused machine learning force fields for 2D materials monolayers

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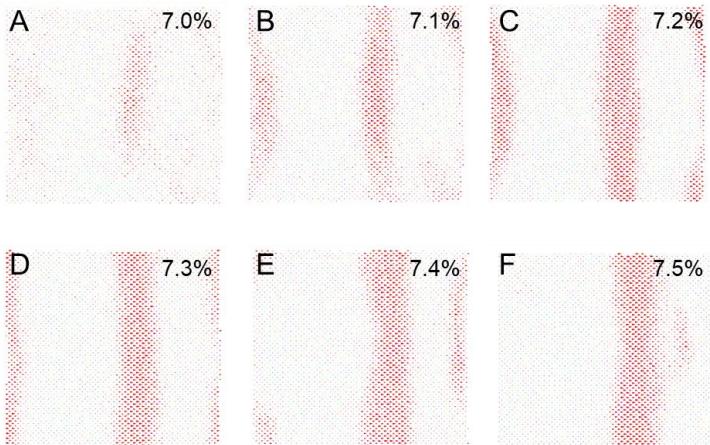
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**Supplementary Table 1.** Comparison the fitting quality by using different adjustable parameters

|             |                | original | $0.1\eta$ | $10\eta$ | $0.1k$ | $10:q$ |
|-------------|----------------|----------|-----------|----------|--------|--------|
| GeSe        | RMSE (eV/atom) | 1.530    | 5.533     | 2.171    | 1.633  | 2.143  |
|             | MAE (eV/atom)  | 1.060    | 3.674     | 1.488    | 1.150  | 1.434  |
|             | $R^2$          | 0.998    | 0.975     | 0.996    | 0.998  | 0.996  |
| PbTe        | RMSE (eV/atom) | 0.920    | 8.337     | 1.353    | 0.920  | 1.426  |
|             | MAE (eV/atom)  | 0.640    | 5.526     | 0.977    | 0.628  | 0.976  |
|             | $R^2$          | 0.999    | 0.923     | 0.998    | 0.999  | 0.998  |
| <i>h</i> BN | RMSE (eV/atom) | 0.840    | 1.004     | 0.773    | 0.625  | 0.660  |
|             | MAE (eV/atom)  | 0.400    | 0.546     | 0.405    | 0.313  | 0.329  |
|             | $R^2$          | 0.9999   | 0.9997    | 0.9998   | 0.9999 | 0.9999 |

**Supplementary Table 2.** Formation energy of point defects in monolayer GeSe, PbTe and *h*BN

|                            | <b>Formation energy</b> | <b>DFT</b> | <b>ML</b> | <b>Relative error</b> |
|----------------------------|-------------------------|------------|-----------|-----------------------|
| Vacancy                    | $E_V^{\text{Ge}}$       | 5.874      | 4.674     | 20.4%                 |
|                            | $E_V^{\text{Se}}$       | 5.879      | 4.912     | 16.4%                 |
|                            | $E_V^{\text{Pb}}$       | 5.564      | 4.231     | 23.9%                 |
|                            | $E_V^{\text{Te}}$       | 4.864      | 5.280     | 8.5%                  |
|                            | $E_V^{\text{B}}$        | 16.564     | 15.552    | 6.1%                  |
|                            | $E_V^{\text{N}}$        | 16.020     | 21.211    | 32.4%                 |
| Anti-sites                 | $E_{\text{GeSe}}^1$     | 1.476      | 1.138     | 22.9%                 |
|                            | $E_{\text{GeSe}}^2$     | 2.522      | 2.486     | 1.4%                  |
|                            | $E_{\text{PbTe}}^1$     | 2.112      | 3.358     | 59.0%                 |
|                            | $E_{\text{PbTe}}^2$     | 2.567      | 2.504     | 2.4%                  |
| Domain boundary<br>(eV/nm) | $E_{\text{hBN}}$        | 7.585      | 9.360     | 23.4%                 |
|                            | GeSe                    | 0.791      | 0.603     | 23.7%                 |
|                            | PbTe                    | 4.467      | 1.124     | 74.8%                 |
| Phase boundary<br>(eV/nm)  |                         |            |           |                       |
| Grain boundary<br>(eV/nm)  | $h\text{BN}$            | 5.967      | 6.740     | 12.9%                 |



**Supplementary Figure 1.** Typical atomic configurations of monolayer PbTe during a stress induced phase transformation at 50 K. (A)-(C) Ferroic phase grows up by the movement of the phase boundary during a typical stress drop from  $\varepsilon = 7.0\%$  to  $\varepsilon = 7.2\%$ ; (D)-(F) Ferroic phase shrinks by the movement of the phase boundary during a typical stress increment from  $\varepsilon = 7.3\%$  to  $\varepsilon = 7.5\%$ .